



2M (128K x 16) Static RAM

Features

- Very high speed: 55 ns and 70 ns
- Temperature Ranges
 - Industrial: -40°C to +85°C
 - Automotive: -40°C to +125°C
- Pin-compatible with the CY62137V
- Ultra-low active power
 - Typical active current: 1.5 mA @ f = 1 MHz
 - Typical active current: 5.5 mA @ f = f_{max} (70-ns speed)
- Low and ultra-low standby power
- Easy memory expansion with $\overline{\text{CE}}$ and $\overline{\text{OE}}$ features
- Automatic power-down when deselected
- CMOS for optimum speed/power
- Packages offered in a Lead-Free and Non-Lead Free 48-ball FBGA

Functional Description^[1]

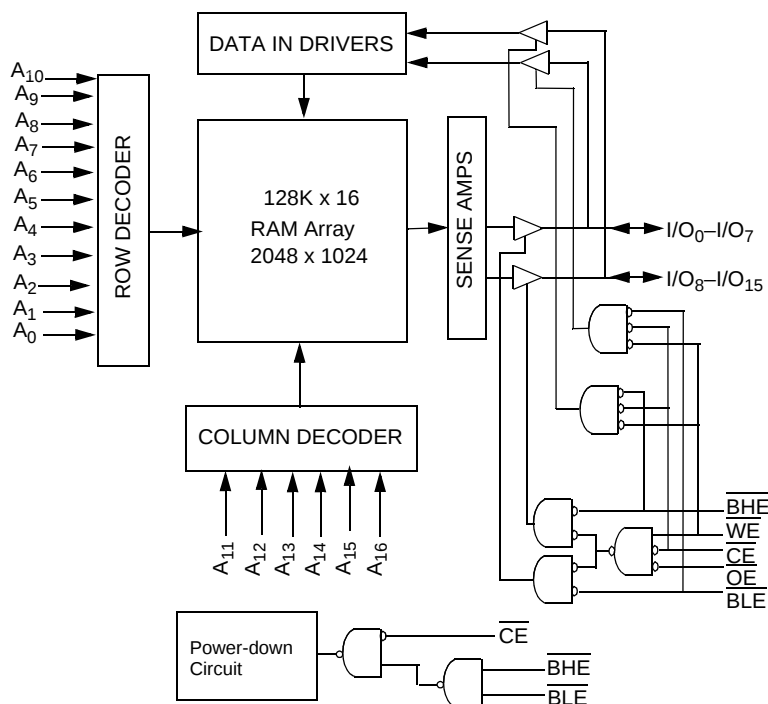
The CY62137CV25/30/33 and CY62137CV are high-performance CMOS static RAMs organized as 128K words by 16 bits. These devices feature advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery

Life™ (MoBL[®]) in portable applications such as cellular telephones. The devices also has an automatic power-down feature that significantly reduces power consumption by 80% when addresses are not toggling. The device can also be put into standby mode reducing power consumption by more than 99% when deselected ($\overline{\text{CE}}$ HIGH or both $\overline{\text{BLE}}$ and $\overline{\text{BHE}}$ are HIGH). The input/output pins (I/O₀ through I/O₁₅) are placed in a high-impedance state when: deselected ($\overline{\text{CE}}$ HIGH), outputs are disabled ($\overline{\text{OE}}$ HIGH), both Byte High Enable and Byte Low Enable are disabled ($\overline{\text{BHE}}$, $\overline{\text{BLE}}$ HIGH), or during a write operation ($\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Write Enable ($\overline{\text{WE}}$) inputs LOW. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from I/O pins (I/O₀ through I/O₇), is written into the location specified on the address pins (A₀ through A₁₆). If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from I/O pins (I/O₈ through I/O₁₅) is written into the location specified on the address pins (A₀ through A₁₆).

Reading from the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable ($\overline{\text{WE}}$) HIGH. If Byte Low Enable ($\overline{\text{BLE}}$) is LOW, then data from the memory location specified by the address pins will appear on I/O₀ to I/O₇. If Byte High Enable ($\overline{\text{BHE}}$) is LOW, then data from memory will appear on I/O₈ to I/O₁₅. See the truth table at the back of this data sheet for a complete description of read and write modes.

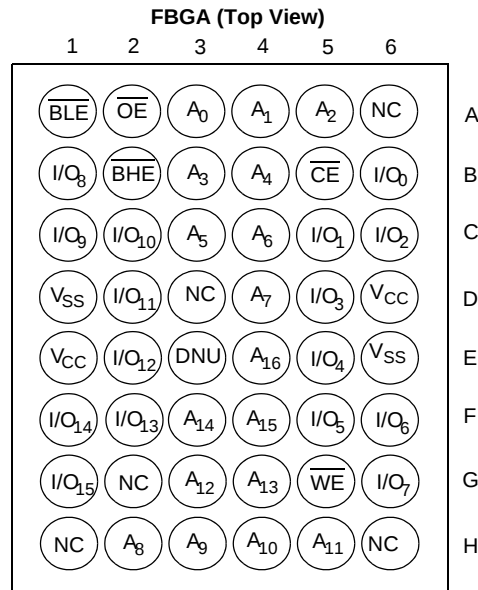
Logic Block Diagram



Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on <http://www.cypress.com>.

Pin Configuration^[2, 3]



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with
Power Applied..... -55°C to +125°C

Supply Voltage to Ground Potential -0.5V to V_{CCMAX} + 0.5V

DC Voltage Applied to Outputs
in High-Z State^[4] -0.5V to V_{CC} + 0.3V

DC Input Voltage^[4] -0.5V to V_{CC} + 0.3V

Output Current into Outputs (LOW) 20 mA

Static Discharge Voltage..... > 2001V
(per MIL-STD-883, Method 3015)

Latch-up Current > 200 mA

Operating Range

Device	Range	Ambient Temperature T _A	V _{CC}
CY62137CV25	Industrial	-40°C to +85°C	2.2V to 2.7V
CY62137CV30			2.7V to 3.3V
CY62137CV33			3.0V to 3.6V
CY62137CV			2.7V to 3.6V
CY62137CV30	Automotive	-40°C to +125°C	2.7V to 3.3V

Product Portfolio

Product	Range	V _{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating, I _{CC} (mA)				Standby, I _{SB2} (μA)	
		f = 1 MHz		f = f _{max}							
		Min.	Typ. ^[5]	Max.		Typ. ^[5]	Max.	Typ. ^[5]	Max.	Typ. ^[5]	Max.
CY62137CV25LL	Industrial	2.2	2.5	2.7	55	1.5	3	7	15	2	10
					70	1.5	3	5.5	12		
CY62137CV30LL	Industrial	2.7	3.0	3.3	55	1.5	3	7	15	2	10
					70	1.5	3	5.5	12		
CY62137CV30LL	Automotive	2.7	3.0	3.3	70	1.5	3	5.5	15	2	15
CY62137CV33LL	Industrial	3.0	3.3	3.6	55	1.5	3	7	15	5	15
					70	1.5	3	5.5	12		
CY62137CVLL	Industrial	2.7V	3.3	3.6	70	1.5	3	5.5	12	5	15
CY62137CVSL	Industrial	2.7V	3.3	3.6	70	1.5	3	5.5	12	1	5

Notes:

- NC pins are not connected to the die.
- E3 (DNU) can be left as NC or V_{SS} to ensure proper application.
- V_{IL(min.)} = -2.0V for pulse durations less than 20 ns.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC(typ.)}, T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	CY62137CV25-55			CY62137CV25-70			Unit
			Min.	Typ. ^[5]	Max.	Min.	Typ. ^[5]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -0.1 mA V _{CC} = 2.2V	2.0			2.0			V
V _{OL}	Output LOW Voltage	I _{OL} = 0.1 mA V _{CC} = 2.2V			0.4			0.4	V
V _{IH}	Input HIGH Voltage		1.8		V _{CC} + 0.3V	1.8		V _{CC} + 0.3V	V
V _{IL}	Input LOW Voltage		-0.3		0.6	-0.3		0.6	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	-1		+1	-1		+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	-1		+1	-1		+1	μA
I _{CC}	V _{CC} Operating Supply Current	f = f _{MAX} = 1/t _{RC} V _{CC} = 2.7V I _{OUT} = 0 mA CMOS Levels		7	15		5.5	12	mA
		f = 1 MHz		1.5	3		1.5	3	
I _{SB1}	Automatic CE Power-down Current—CMOS Inputs	CE ≥ V _{CC} - 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = f _{max} (Address and Data Only), f=0 (OE, WE, BHE, and BLE)		2	10		2	10	μA
I _{SB2}	Automatic CE Power-down Current—CMOS Inputs	CE ≥ V _{CC} - 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = 0, V _{CC} = 2.7V							

Parameter	Description	Test Conditions	CY62137CV30-55			CY62137CV30-70			Unit
			Min.	Typ. ^[5]	Max.	Min.	Typ. ^[5]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -1.0 mA V _{CC} = 2.7V	2.4			2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 2.1 mA V _{CC} = 2.7V			0.4			0.4	V
V _{IH}	Input HIGH Voltage		2.2		V _{CC} + 0.3V	2.2		V _{CC} + 0.3V	V
V _{IL}	Input LOW Voltage		-0.3		0.8	-0.3		0.8	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}	Ind'l	-1	+1	-1		+1	μA
			Auto			-2		+2	
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled	Ind'l	-1	+1	-1		+1	μA
			Auto			-2		+2	
I _{CC}	V _{CC} Operating Supply Current	f = f _{MAX} = 1/t _{RC} V _{CC} = 3.3V I _{OUT} = 0 mA CMOS Levels	Ind'l		7	15		5.5	mA
			Auto					5.5	
		f = 1 MHz			1.5	3		1.5	
I _{SB1}	Automatic CE Power-down Current—CMOS Inputs	CE ≥ V _{CC} - 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V, f = f _{max} (Address and Data Only), f=0 (OE, WE, BHE, and BLE)	Ind'l		2	10		2	μA
			Auto					2	
I _{SB2}	Automatic CE Power-down Current—CMOS Inputs	CE ≥ V _{CC} - 0.2V V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V f = 0, V _{CC} = 3.3V	Ind'l		2	10		2	μA
			Auto					2	

Electrical Characteristics Over the Operating Range

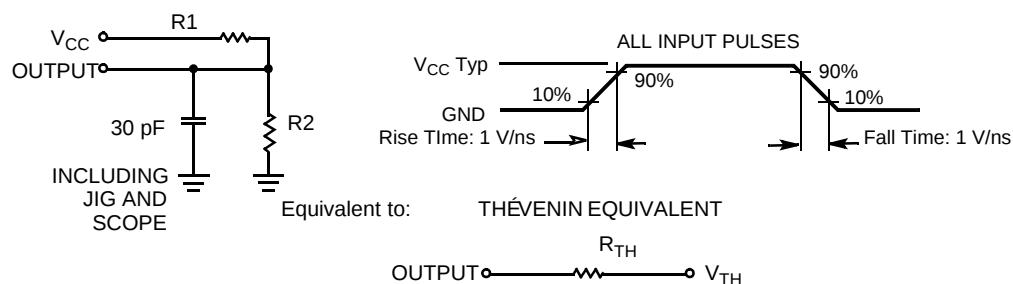
Parameter	Description	Test Conditions		CY62137CV33-55			CY62137CV33-70 CY62137CV-70			Unit
				Min.	Typ. ^[5]	Max.	Min.	Typ. ^[5]	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = −1.0 mA	V _{CC} = 3.0V	2.4			2.4			V
			V _{CC} = 2.7V				2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 2.1 mA	V _{CC} = 3.0V			0.4			0.4	V
			V _{CC} = 2.7V						0.4	V
V _{IH}	Input HIGH Voltage			2.2		V _{CC} + 0.3V	2.2		V _{CC} + 0.3V	V
V _{IL}	Input LOW Voltage			−0.3		0.8	−0.3		0.8	V
I _{IX}	Input Leakage Current	GND ≤ V _I ≤ V _{CC}		−1		+1	−1		+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _O ≤ V _{CC} , Output Disabled		−1		+1	−1		+1	μA
I _{CC}	V _{CC} Operating Supply Current	f = f _{MAX} = 1/t _{RC}	V _{CC} = 3.6V I _{OUT} = 0 mA CMOS Levels		7	15		5.5	12	mA
		f = 1 MHz			1.5	3		1.5	3	
I _{SB1}	Automatic CE Power-down Current —CMOS Inputs	CE ≥ V _{CC} − 0.2V V _{IN} ≥ V _{CC} − 0.2V or V _{IN} ≤ 0.2V, f = f _{max} (Address and Data Only), f=0 (OE, WE, BHE, and BLE)			5	15		5	15	μA
I _{SB2}	Automatic CE Power-down Current —CMOS Inputs	CE ≥ V _{CC} − 0.2V V _{IN} ≥ V _{CC} − 0.2V or V _{IN} ≤ 0.2V, f = 0, V _{CC} = 3.6V			5	15		5	15	
								1	5	

Capacitance^[6]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz,	6	pF
C _{OUT}	Output Capacitance	V _{CC} = V _{CC} (typ.)	8	pF

Thermal Resistance

Parameter	Description	Test Conditions	BGA	Unit
Θ _{JA}	Thermal Resistance (Junction to Ambient) ^[6]	Still Air, soldered on a 3 x 4.5 inch, two-layer printed circuit board	55	°C/W
Θ _{JC}	Thermal Resistance (Junction to Case) ^[6]		16	°C/W

AC Test Loads and Waveforms


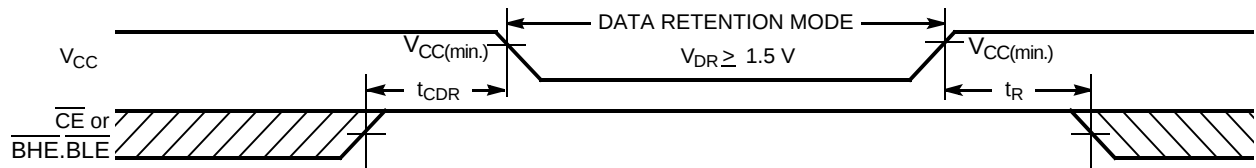
Parameters	2.5V	3.0V	3.3V	Unit
R1	16600	1105	1216	Ω
R2	15400	1550	1374	Ω
R _{TH}	8000	645	645	Ω
V _{TH}	1.20	1.75	1.75	V

Note:

6. Tested initially and after any design or process changes that may affect these parameters.

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions		Min.	Typ. ^[5]	Max.	Unit
V_{DR}	V_{CC} for Data Retention			1.5		V_{CCmax}	V
I_{CCDR}	Data Retention Current	$V_{CC} = 1.5V$ $CE \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	LL Auto SL	Ind'l Auto Ind'l	1	6 8 4	μA
$t_{CDR}^{[6]}$	Chip Deselect to Data Retention Time			0			ns
$t_R^{[7]}$	Operation Recovery Time			t_{RC}			ns

Data Retention Waveform^[8]

Switching Characteristics Over the Operating Range^[9]

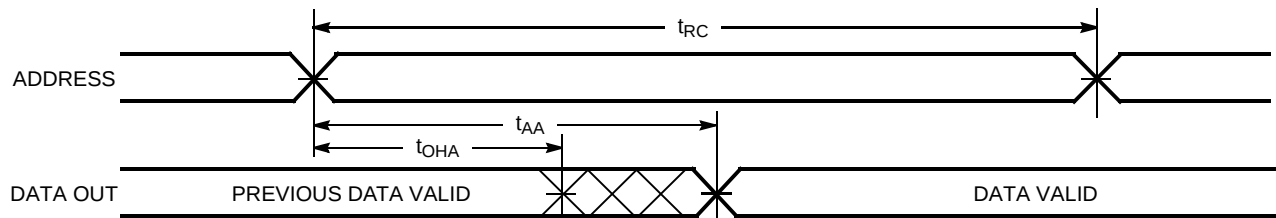
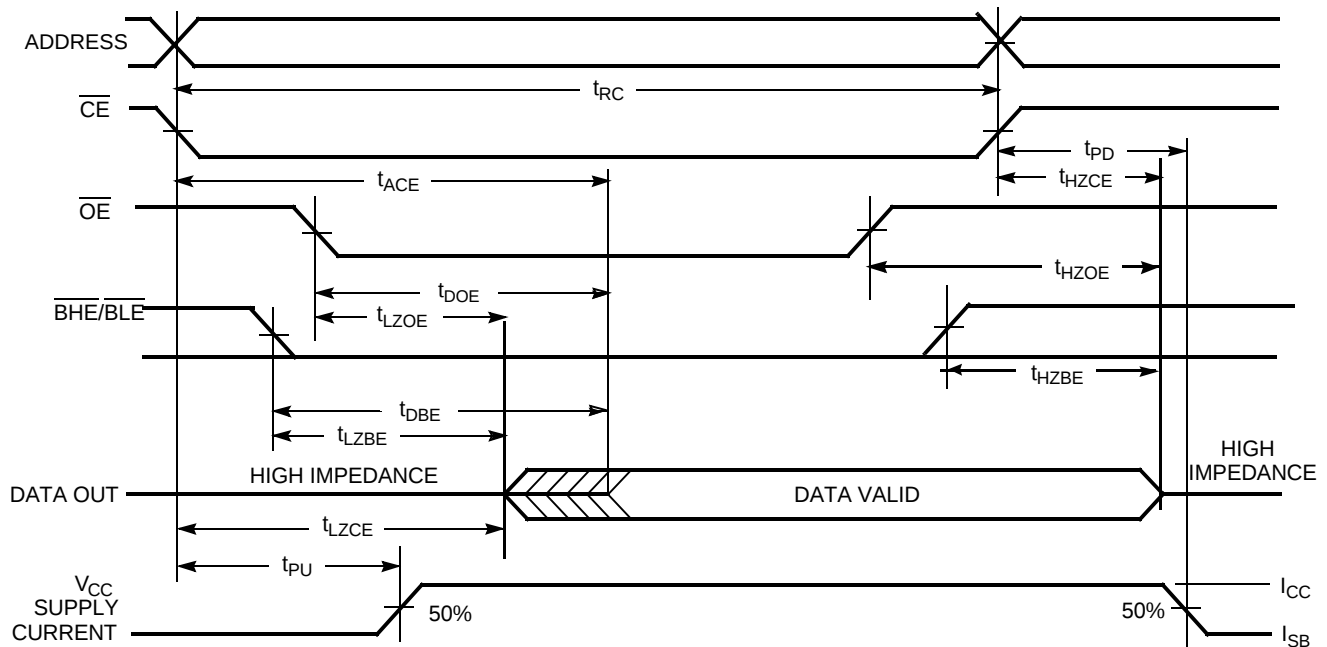
Parameter	Description	55 ns		70 ns		Unit
		Min	Max	Min	Max	
Read Cycle						
t _{RC}	Read Cycle Time	55		70		ns
t _{AA}	Address to Data Valid		55		70	ns
t _{OHA}	Data Hold from Address Change	10		10		ns
t _{ACE}	$\overline{\text{CE}}$ LOW to Data Valid		55		70	ns
t _{DOE}	$\overline{\text{OE}}$ LOW to Data Valid		25		35	ns
t _{LZOE}	$\overline{\text{OE}}$ LOW to Low-Z ^[10]	5		5		ns
t _{HZOE}	$\overline{\text{OE}}$ HIGH to High-Z ^[10, 12]		20		25	ns
t _{LZCE}	$\overline{\text{CE}}$ LOW to Low-Z ^[10]	10		10		ns
t _{HZCE}	$\overline{\text{CE}}$ HIGH to High-Z ^[10, 12]		20		25	ns
t _{PU}	$\overline{\text{CE}}$ LOW to Power-up	0		0		ns
t _{PD}	$\overline{\text{CE}}$ HIGH to Power-down		55		70	ns
t _{DBE}	$\overline{\text{BHE}}/\overline{\text{BLE}}$ LOW to Data Valid		55		70	ns
t _{LZBE} ^[11]	$\overline{\text{BHE}}/\overline{\text{BLE}}$ LOW to Low-Z ^[10]	5		5		ns
t _{HZBE}	$\overline{\text{BHE}}/\overline{\text{BLE}}$ HIGH to High-Z ^[10, 12]		20		25	ns
Write Cycle ^[13]						
t _{WC}	Write Cycle Time	55		70		ns
t _{SCE}	$\overline{\text{CE}}$ LOW to Write End	45		60		ns
t _{AW}	Address Set-up to Write End	45		60		ns

Notes:

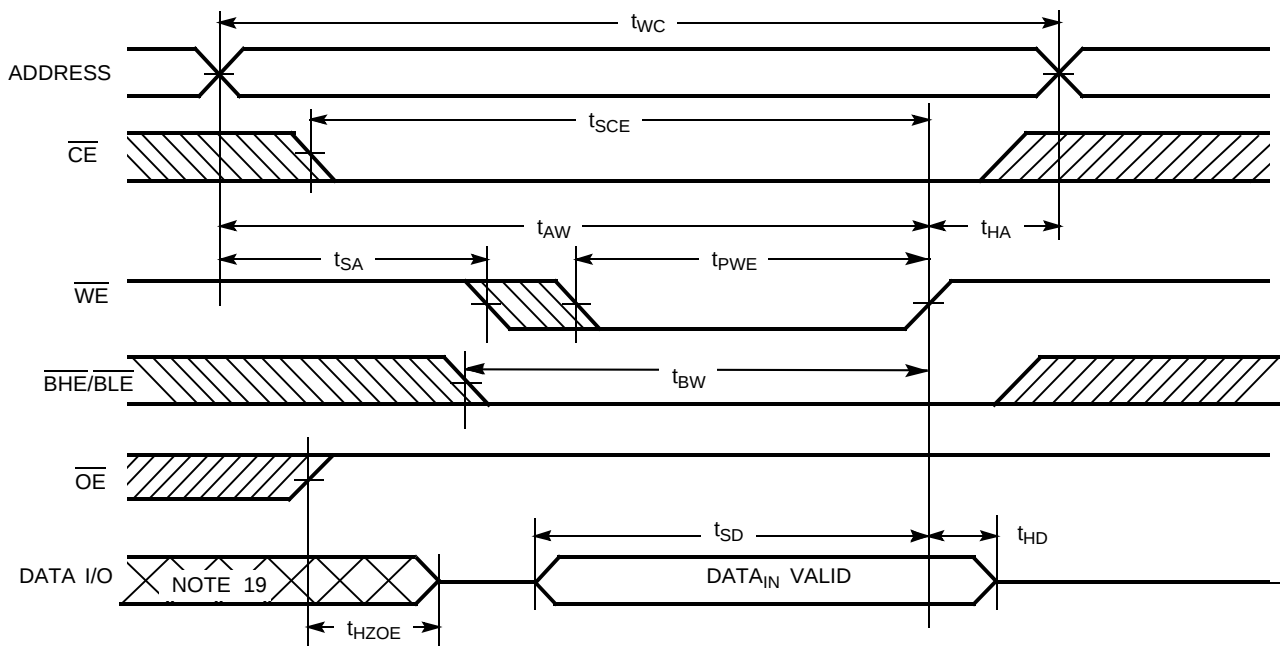
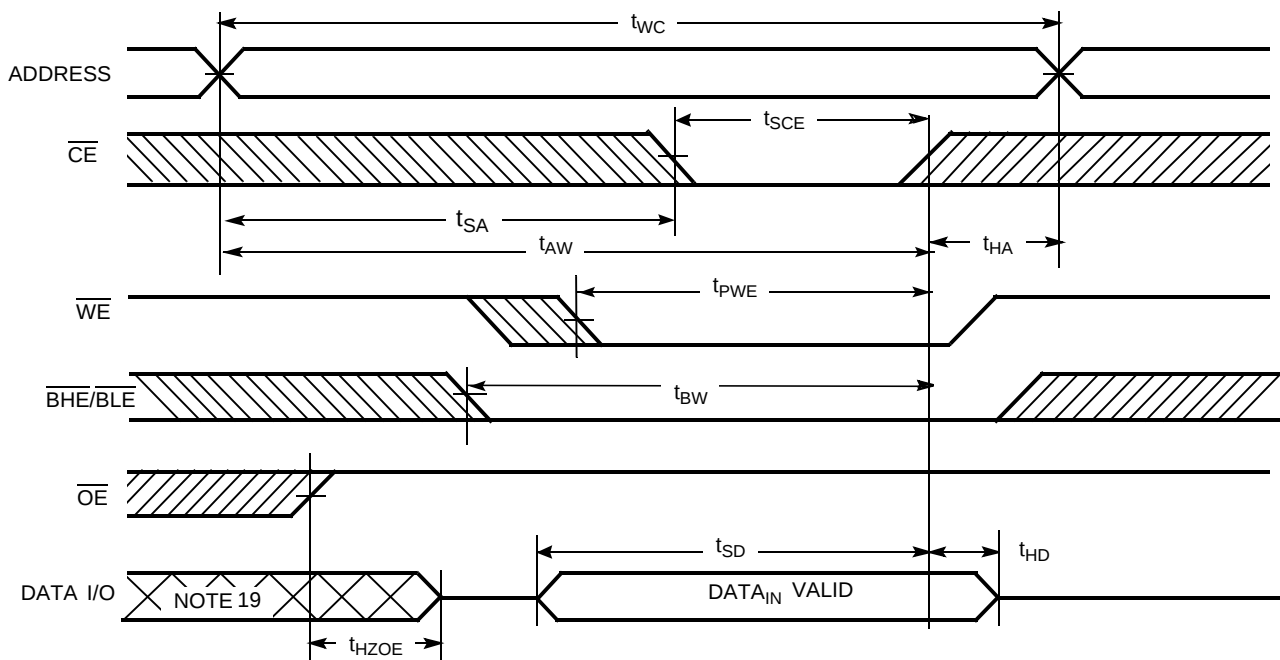
- Full-device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} > 100 \mu s$ or stable at $V_{CC(min.)} > 100 \mu s$.
- $\overline{BHE}/\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0 to $V_{CC(typ.)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- If both byte enables are toggled together this value is 10 ns.
- t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
- The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE} = V_{IL}$, $\overline{BHE}$ and/or $\overline{BLE} = V_{IL}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Characteristics Over the Operating Range^[9] (continued)

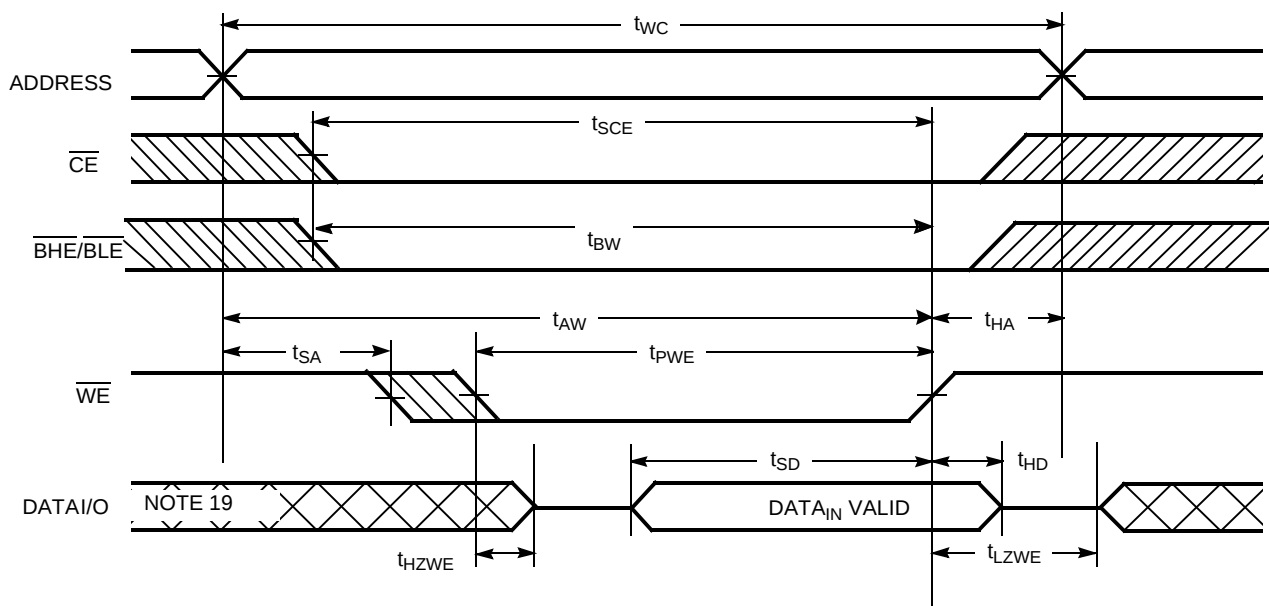
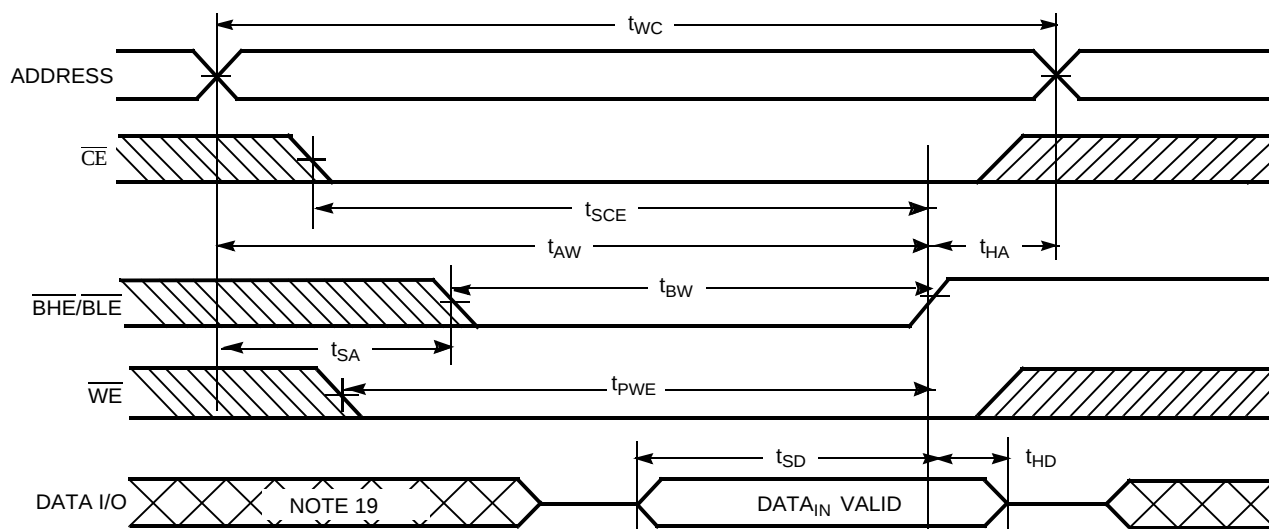
Parameter	Description	55 ns		70 ns		Unit
		Min	Max	Min	Max	
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		ns
t_{PWE}	WE Pulse Width	40		45		ns
t_{BW}	$\overline{BHE}/\overline{BLE}$ Pulse Width	50		60		ns
t_{SD}	Data Set-up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	WE LOW to High-Z ^[10, 12]		20		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z ^[10]	10		10		ns

Switching Waveforms
Read Cycle No. 1 (Address Transition Controlled)^[14, 15]

Read Cycle No. 2 ($\overline{OE}$ Controlled)^[15, 16]

Notes:

14. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL} , $\overline{BHE}$, $\overline{BLE}$ = V_{IL} .
15. $\overline{WE}$ is HIGH for read cycle.
16. Address valid prior to or coincident with $\overline{CE}$, $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)
Write Cycle No. 1 ($\overline{\text{WE}}$ Controlled)^[13, 17, 18]

Write Cycle No. 2 ($\overline{\text{CE}}$ Controlled)^[13, 17, 18]

Notes:

17. Data I/O is high-impedance if $\overline{\text{OE}} = V_{\text{IL}}$.
18. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ HIGH, the output remains in a high-impedance state.
19. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)
Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[18]

Write Cycle No. 4 ($\overline{\text{BHE/BLE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[18]




Truth Table

CE	WE	OE	BHE	BLE	Inputs/Outputs	Mode	Power
H	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
X	X	X	H	H	High-Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High-Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High-Z	Read	Active (I_{CC})
L	H	H	L	L	High-Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High-Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High-Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_0 – I/O_7); I/O_8 – I/O_{15} in High-Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8 – I/O_{15}); I/O_0 – I/O_7 in High-Z	Write	Active (I_{CC})

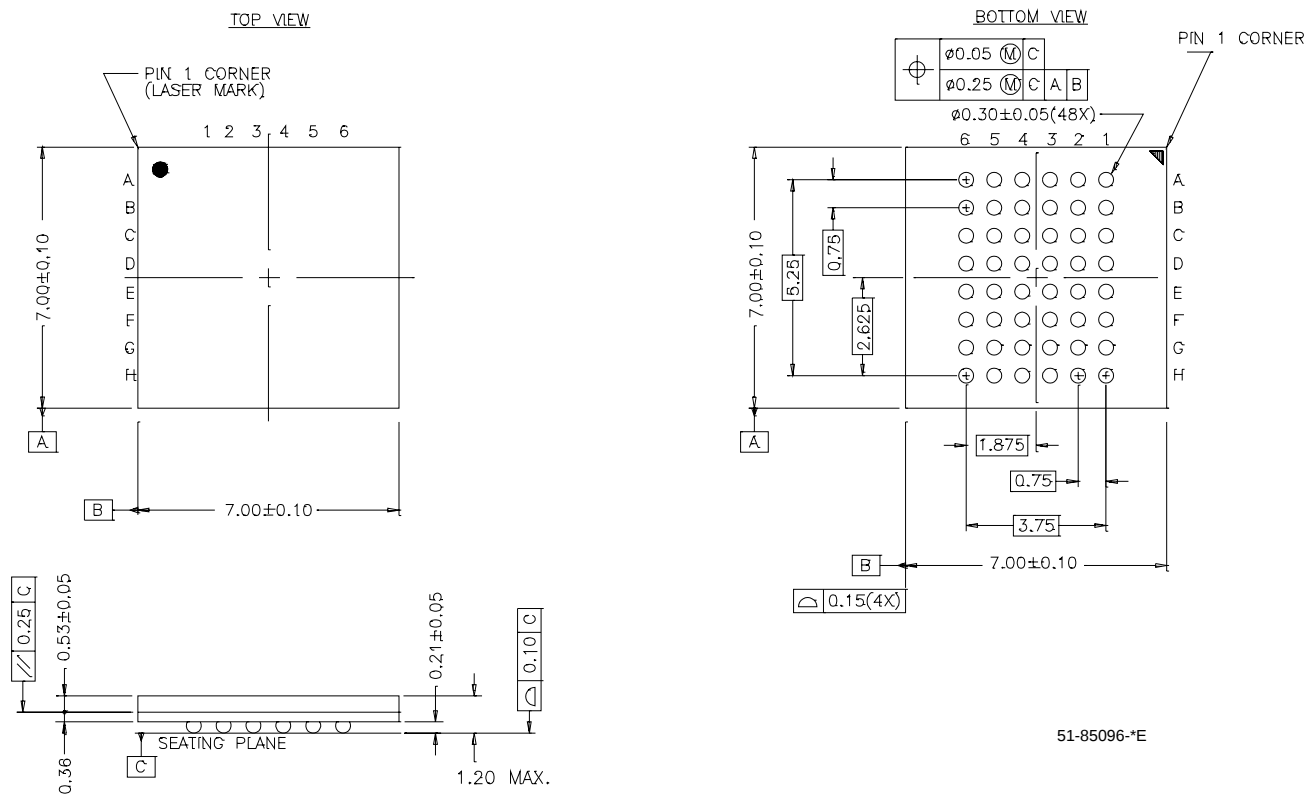
Ordering Information

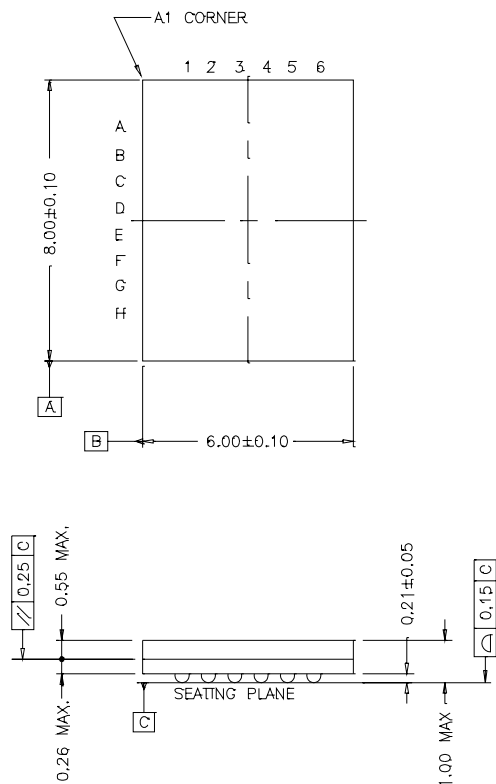
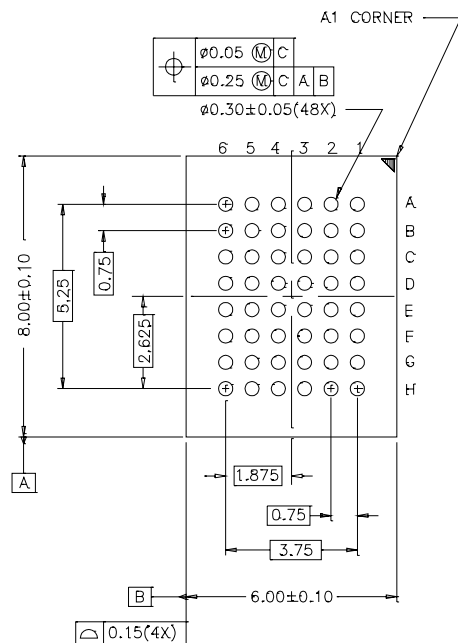
Speed (ns)	Ordering Code	Voltage Range (V)	Package Name	Package Type	Operating Range
70	CY62137CV25LL-70BAI	2.2–2.7	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	Industrial
	CY62137CV25LL-70BVI	2.2–2.7	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CV30LL-70BAI	2.7–3.3	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CV30LL-70BVI	2.7–3.3	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CV30LL-70BAXE	2.7–3.3	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm) (Pb-Free)	Automotive
	CY62137CV30LL-70BVXE	2.7–3.3	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm) (Pb-Free)	
	CY62137CV33LL-70BAI	3.0–3.6	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	Industrial
	CY62137CV33LL-70BVI	3.0–3.6	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CVLL-70BAI	2.7–3.6	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CVLL-70BVI	2.7–3.6	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CVSL-70BAI	2.7–3.6	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CVSL-70BVI	2.7–3.6	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
55	CY62137CV25LL-55BAI	2.2–2.7	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CV25LL-55BVI	2.2–2.7	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CV30LL-55BAI	2.7–3.3	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CV30LL-55BVI	2.7–3.3	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	
	CY62137CV33LL-55BAI	3.0–3.6	BA48A	48-ball Fine Pitch BGA (7 mm x 7 mm x 1.2 mm)	
	CY62137CV33LL-55BVI	3.0–3.6	BV48A	48-ball Fine Pitch BGA (6 mm x 8 mm x 1 mm)	

Shaded areas contain advance information. Please contact your local sales representative for availability of these parts.

Package Diagrams

48-ball (7.00 mm x 7.00 mm x 1.2 mm) FBGA BA48A



Package Diagrams (continued)
48-Lead VFBGA (6 x 8 x 1 mm) BV48A
TOP VIEW

BOTTOM VIEW


51-85150-*B

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Document History Page

Document Title: CY62137CV25/30/33 MoBL [®] and CY62137CV MoBL [®] 2M (128K x 16) Static RAM Document Number: 38-05201				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	112393	02/19/02	GAV	New Data Sheet (advance information)
*A	114015	04/25/02	JUI	Added BV package diagram Changed from Advance Information to Preliminary
*B	117064	07/12/02	MGN	Changed from Preliminary to Final
*C	118122	09/10/02	MGN	Added new part number: CY62137CV with wider voltage (2.7V – 3.6V). Added new SL power bin for new part number. For T _{AA} = 55 ns, improved t _{PWE} min. from 45 ns to 40 ns. For T _{AA} = 70 ns, improved t _{PWE} min. from 50 ns to 45 ns. For T _{AA} = 70 ns, improved t _{LZWE} min. from 5 ns to 10 ns.
*D	118761	09/23/02	MGN	Improved Typ. I _{CC} spec to 7 mA (for 55 ns) and 5.5 mA (for 70 ns). Improved Max I _{CC} spec to 15 mA (for 55 ns) and 12 mA (for 70 ns). For T _{AA} = 55 ns, improved t _{LZWE} min. from 5 ns to 10 ns. Changed upper spec. for Supply Voltage to Ground Potential to V _{CCMAX} + 0.5V. Changed upper spec. for DC Voltage Applied to Outputs in High-Z State and DC Input Voltage to V _{CC} + 0.3V.
*E	343877	See ECN	PCI	Added Automotive Information in Operating Range, DC and Ordering Information Table